

PNP Epitaxial Silicon Transistor

1 Description

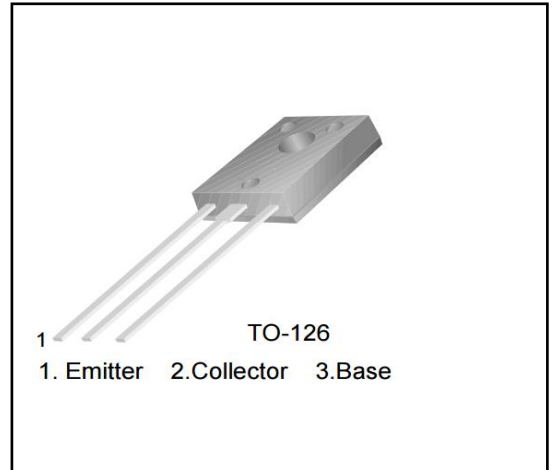
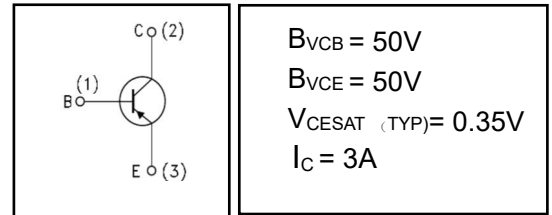
The 2SB772 is a medium power low voltage transistor

2 Features

- High current output up to 3A
- Low saturation voltage
- Complement to 2SD882

3 Applications

- audio power amplifier,
- DC-DC converter
- voltage regulator.



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	- 50	V
Collector-Emitter Voltage	V_{CEO}	- 50	V
Emitter-Base Voltage	V_{EBO}	- 5	V
Collector Current (DC)	I_C	- 3	A
*Collector Current (Pulse)	I_{CP}	- 7	A
Base Current (DC)	I_B	- 0.6	A
Collector Dissipation (TC=25°C)	P_C	10	W
Collector Dissipation (Ta=25°C)		1	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	- 55 ~ 150	°C

* PW≤10ms, Duty Cycle≤50%

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	R_{thJC}	13.5	°C/W
Thermal Resistance, Junction to Ambient	R_{thJA}	132	°C/W

4.3 Electrical Characteristics (Tc=25°C, unless otherwise noted)

SYMBOL	PARAMETER	Test Conditions	Min	Typ	Max	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} =-50V	-	-	10	uA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} =-50V	-	-	50	uA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} =-5V	-	-	10	uA
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C =-10mA	50	58	-	V
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C =-100uA	50	90	-	V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E =-100uA	5	11.5	-	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =-1A I _B =-50mA	-	0.23	0.4	V
		I _C =-2A I _B =-200mA	-	0.35	0.5	
		I _C =-3A I _B =-150mA	-	0.5	0.8	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C =-2A I _B =-200mA	-	1.05	1.8	
h _{FE}	DC Current Gain	I _C =-100mA, V _{CE} =-2V	100	-	400	
		I _C =-1A, V _{CE} =-2 V	100	250	350	
		I _C =-3A, V _{CE} =-2 V	50	-	300	
		I _C =-0.5A, V _{CE} =-5 V*	150	270	350	
f _T	Transition Frequency	V _{CE} =-5V, I _C =-100mA, f=10MHZ	-	50	-	MHZ

h_{FE}* Classification

Classification	1	2	3	4	5
h _{FE} *	170-210	210-230	230-260	260-290	290-320

5 Typical characteristics diagrams

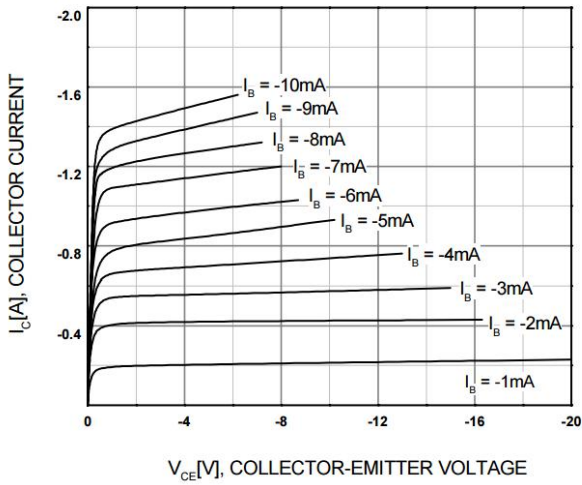


Figure 1. Static Characteristic

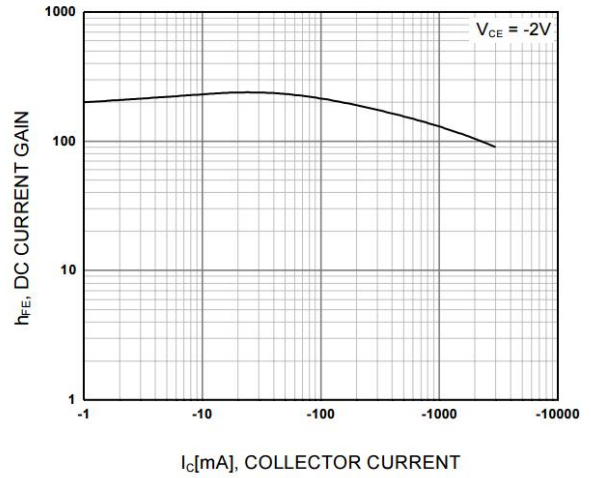
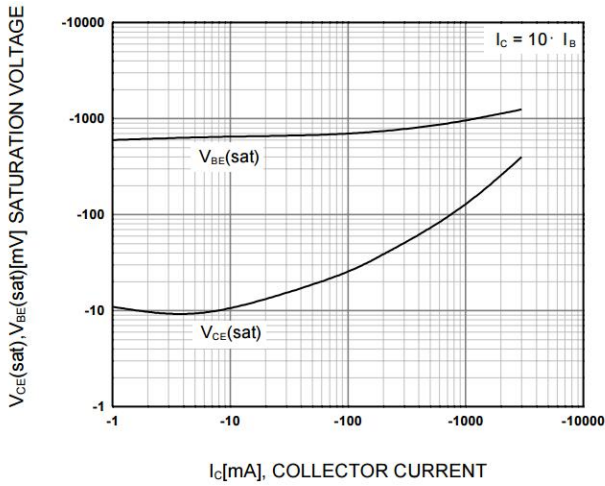


Figure 2. DC current Gain



**Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**

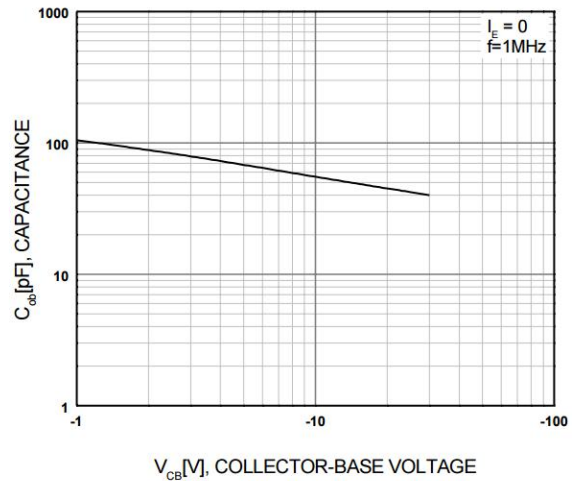


Figure 4. Collector Output Capacitance

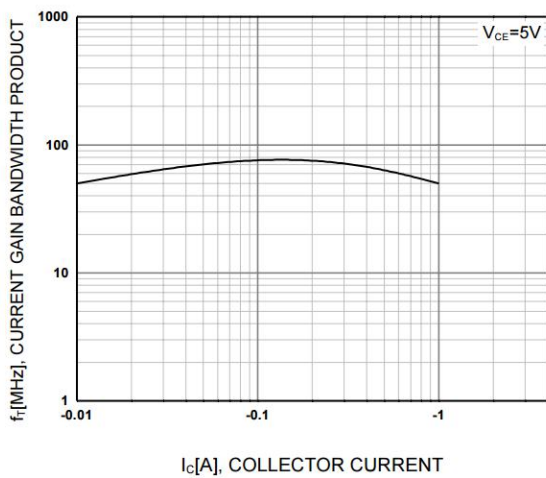


Figure 5. Current Gain Bandwidth Product

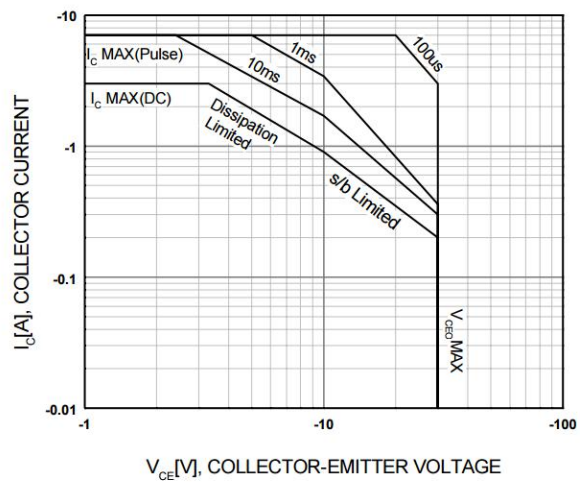


Figure 6. Safe Operating Area

5 Typical characteristics diagrams(continues)

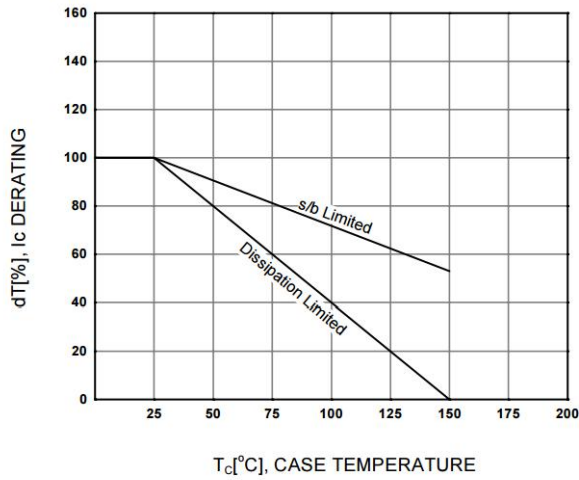


Figure 7. Derating Curve of Safe Operating Areas

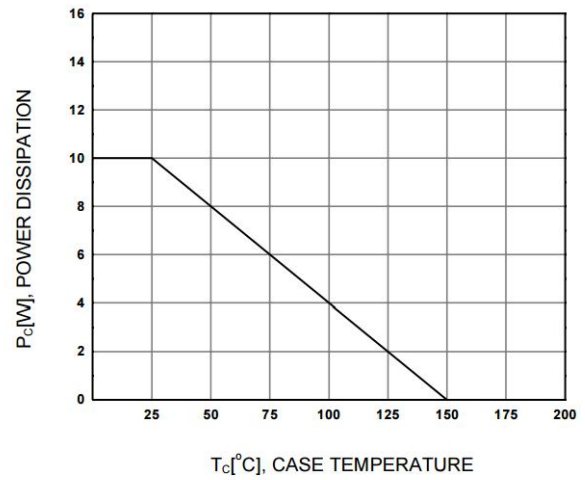


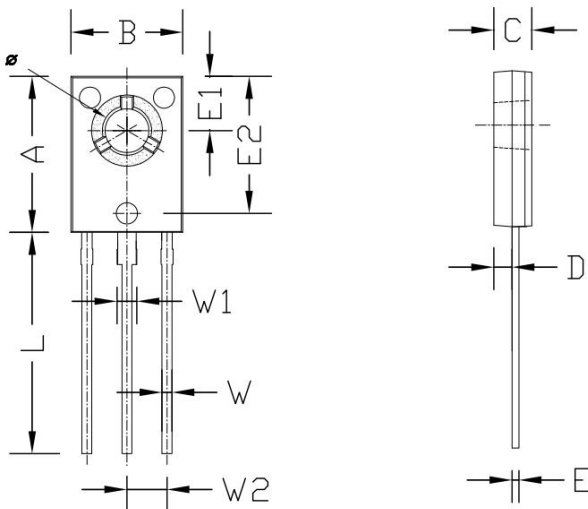
Figure 8. Power Derating

6 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
2SB772	TO-126	B772	Pb-free	bag	200/bag

7 Dimensions

TO-126 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	10.50	11.10	0.413	0.437
B	7.65	7.95	0.301	0.313
C	2.50	2.80	0.098	0.110
D	1.45	1.75	0.057	0.069
E	0.40	0.60	0.016	0.024
E1	3.65	3.85	0.144	0.152
E2	9.40	9.60	0.370	0.378
L	15.4	15.9	0.606	0.626
W	0.60	0.80	0.024	0.031
W1	1.20	1.30	0.047	0.051
W2	2.32 TYP		0.091 TYP	
Φ	3.05	3.35	0.120	0.132

8 Attentions

- ROUM Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Roma products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

9 Appendix

Revision history:

Date	REV.	Description	Page
2017.04.11	1.0	Original	